Mark for indicating

LED side φ1.5

16 0+0

14.0+

(10.0)

.0 min

02.2±0

4-00.45

Unit: mm

(2.54)

1: Cathode 2: Anode

3. Emitter 4: Collector

PRSTR104-001 Package

CNZ2152 (ON2152)

Reflective photosensor

Non-contact point SW, object sensing

Overview

CNZ2152 is a photosensor detecting the change of reflective light in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a high sensitivity Si phototransistor is used as the light detecting element. The two elements are located parallel in the same direction and objects are detected when passing in front of the device.

Features

- Fast response
- Applications
- Detection of paper, film and cloth Optical mark reading

• High sensitivity

- Detection of coin and bill • Detection of position and edge
- Start, end mark detection of magnetic tape

Absolute Maximum Ratings $T_a = 25^{\circ}C$

						rKSIKI04-001 rad
Parameter		Symbol	Rating	Unit	\mathbf{i}	(Note) / Dimension is reference
Input (Light	Reverse voltage	V _R	3	V	-	\sim
emitting diode)	Forward current	I _F	100	mA		\searrow
	Power dissipation *1	P _D	150	mW	\smile)
Output (Photo	Collector-emitter voltage	V _{CEO}	20	/v	\smile	
transistor)	(Base open)			/		
	Emitter-collector voltage	V _{ECO}	3	V		
	(Base open)		\square			
	Collector current	I _C	30 <	mA		Note) *1: Input power derating ratio is
	Collector power dissipation *2	P _C	(150)	mW		2.0 mW/°C at $T_a \ge 25^{\circ}C$.
Temperature	Operating ambient temperature	Topr	-25 to +85	°C		*2: Output power derating ratio is
	Storage temperature	T _{stg}	-30 to +100	°C		2.0 mW/°C at $T_a \ge 25^{\circ}C$.

· High SN ratio

Electrical-Optical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

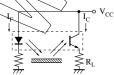
	Parameter	Symbol	\sum	Conditions	Min	Тур	Max	Unit
Input	Forward voltage	V _F	I₽Ę	100 mA		1.25	1.50	V
characteristics	Reverse current	I _R	V _R =	= 5 V			10	μΑ
Output	Collector-emitter cutoff current	, I _{CEO}	V _{CE}	= 10 V		0.05	2.00	μΑ
characteristics	(Base open)	\bigvee						
Transfer	Collector current	I _C *2	V _{CC}	= 5 V, I_F = 20 mA, R_L = 100 Ω	0.8	3.0		mA
characteristics		I _C *3				500		μΑ
	Collector-envitter saturation voltage	V _{CE(sat)}	$I_F =$	100 mA, I _C = 1 mA			0.6	V
	Rise time	t _r	V _{CC}	= 10 V, I_C = 1 mA, R_L = 100 Ω		8		μs
	Falltime	t _f				8		μs

Note) 1. Input and output are handled electrically.

2. This product is not designed to withstand radiation

*X: Output current measurement circuit (Ambient light is shut off completely)

Test Paper

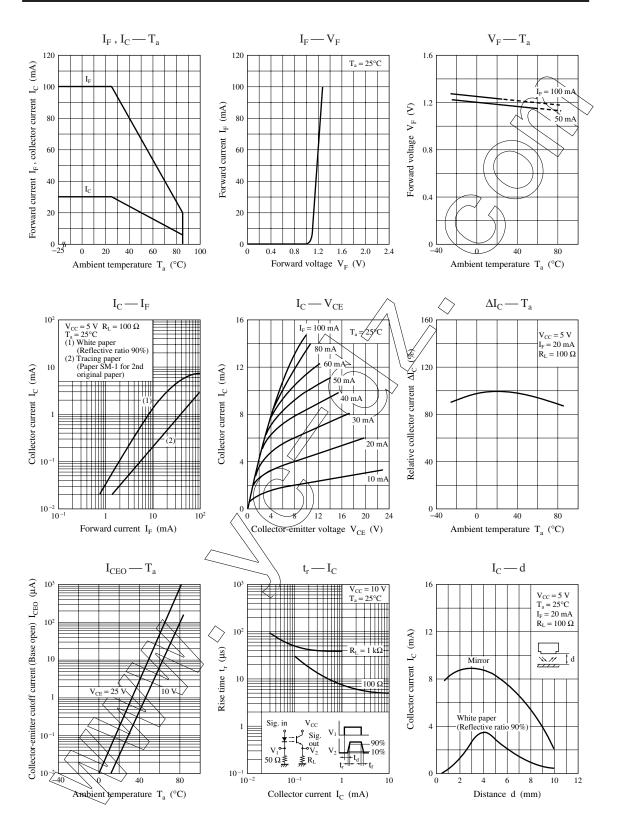


*2: White paper (reflective ratio 90%) d = 5 mm

*3: Tracing paper (paper SM-1 for 2nd original paper)

Note) The part number in the parenthesis shows conventional part number.

3



A Caution for Safety

A DANGER

This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded form general industrial waste or household garbage.

Request for your special attention and precautions in using the technical information and semiconductors described in this material

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